

23. (Amended) [A semiconductor device] A method for fabricating the semiconductor device according to claim 21, wherein

in the contact hole forming step, the first insulation film is etched with a photoresist including an opening extended over the word lines, and the etching stopper film as a mask to form a plurality of the contact holes in the opening.

24. (Amended) [A semiconductor device] A method for fabricating the semiconductor device according to claim 19, further comprising before the bit line forming step, a plug forming step of forming a plug buried in the contact hole.

25. (Amended) [A semiconductor device] A method for fabricating the semiconductor device according to claim 20, further comprising before the bit line forming step, a plug forming step of forming a plug buried in the contact hole.

26. (Amended) [A semiconductor device] A method for fabricating the semiconductor device according to claim 21, further comprising before the bit line forming step, a plug forming step of forming a plug buried in the contact hole.